

Solar Selective Absorber

Coating Methods – Plasma Processes

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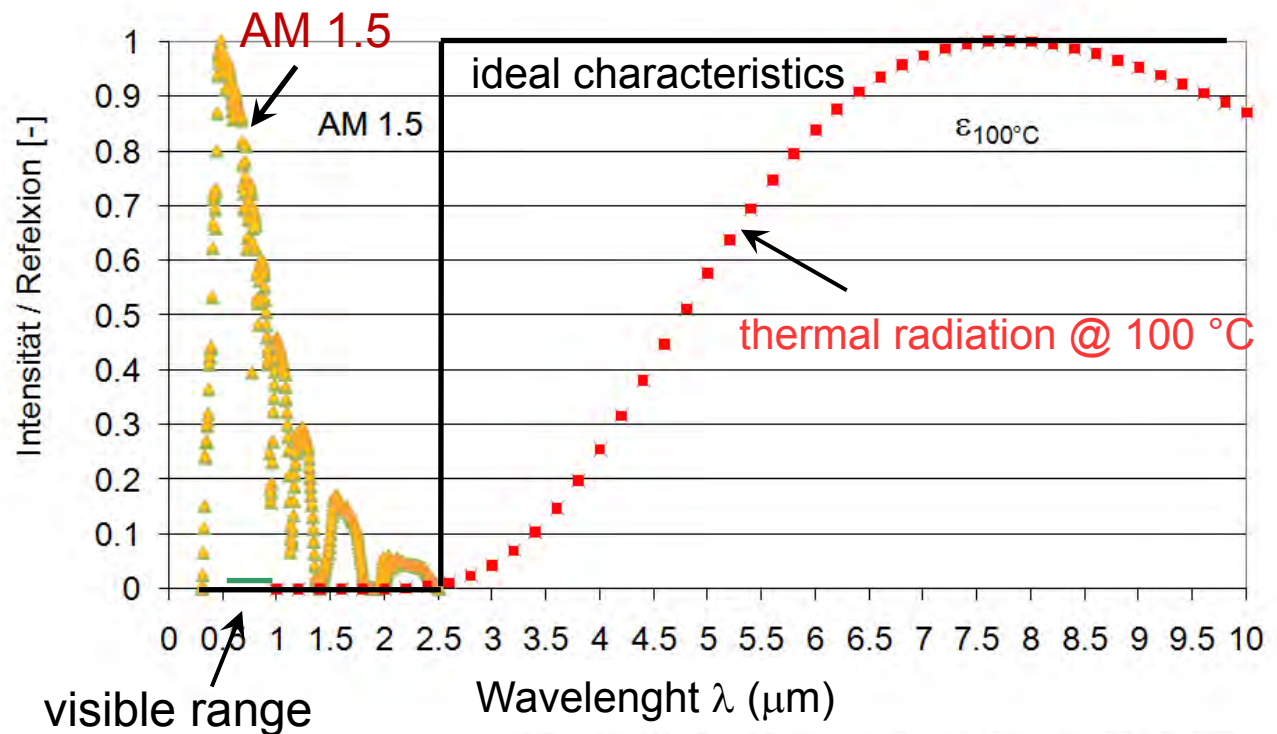
■ Optical properties of a selective absorber

Optical properties of solar selective absorbers $(\alpha_{AM1.5} / \varepsilon_{T^{\circ}C})$

Wien's displacement law:

$$\lambda_{\max} = \frac{2897,8 \mu\text{m} \cdot \text{K}}{T}$$

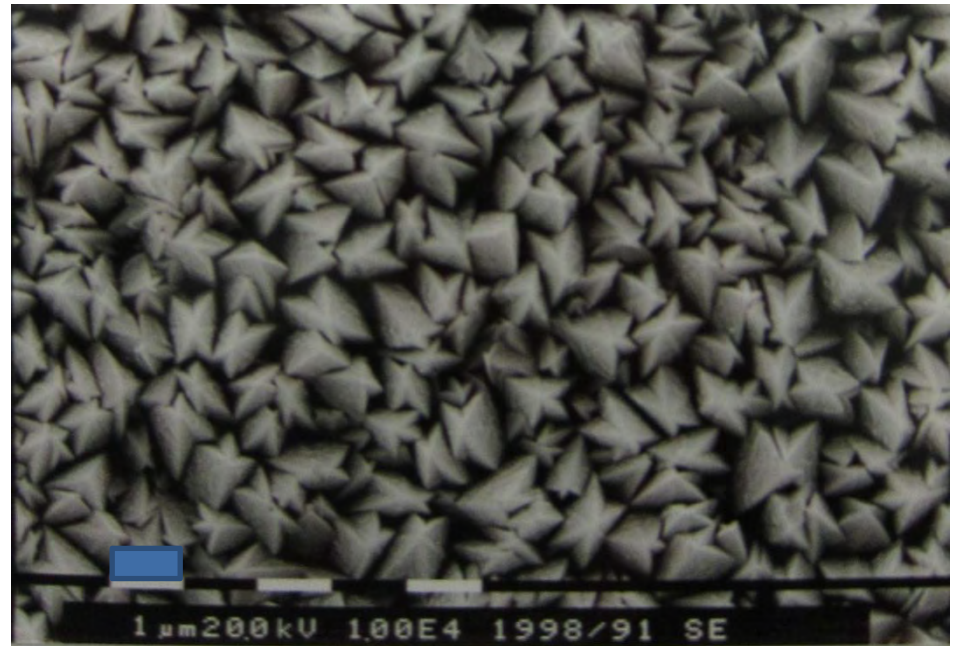
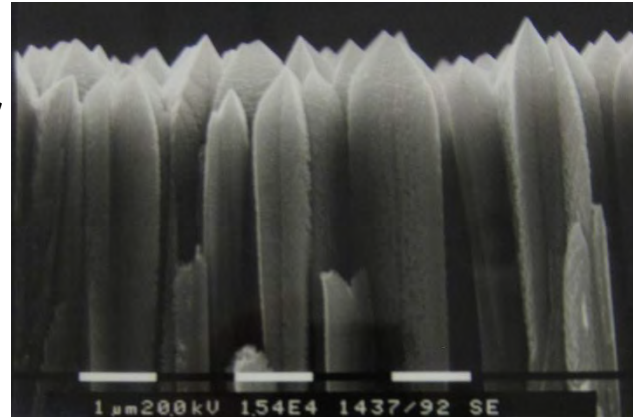
Temperature T (°C)	Wavelength $\lambda_{\max}$ (μm)
200	6.1
250	5.55
300	5.05
500	3.75
600	3.33



Thermodynamics: 2. Law $\varepsilon(\lambda, T) = \alpha(\lambda, T)$

■ Design types of selective absorber

- Intrinsic selective material
- Surface texture / geometrical structure
- Semiconductor-Metal Combination
- Multilayers
- Metal-Dielectric
- Solar-transmitting / Blackbody-like



Nb on Si

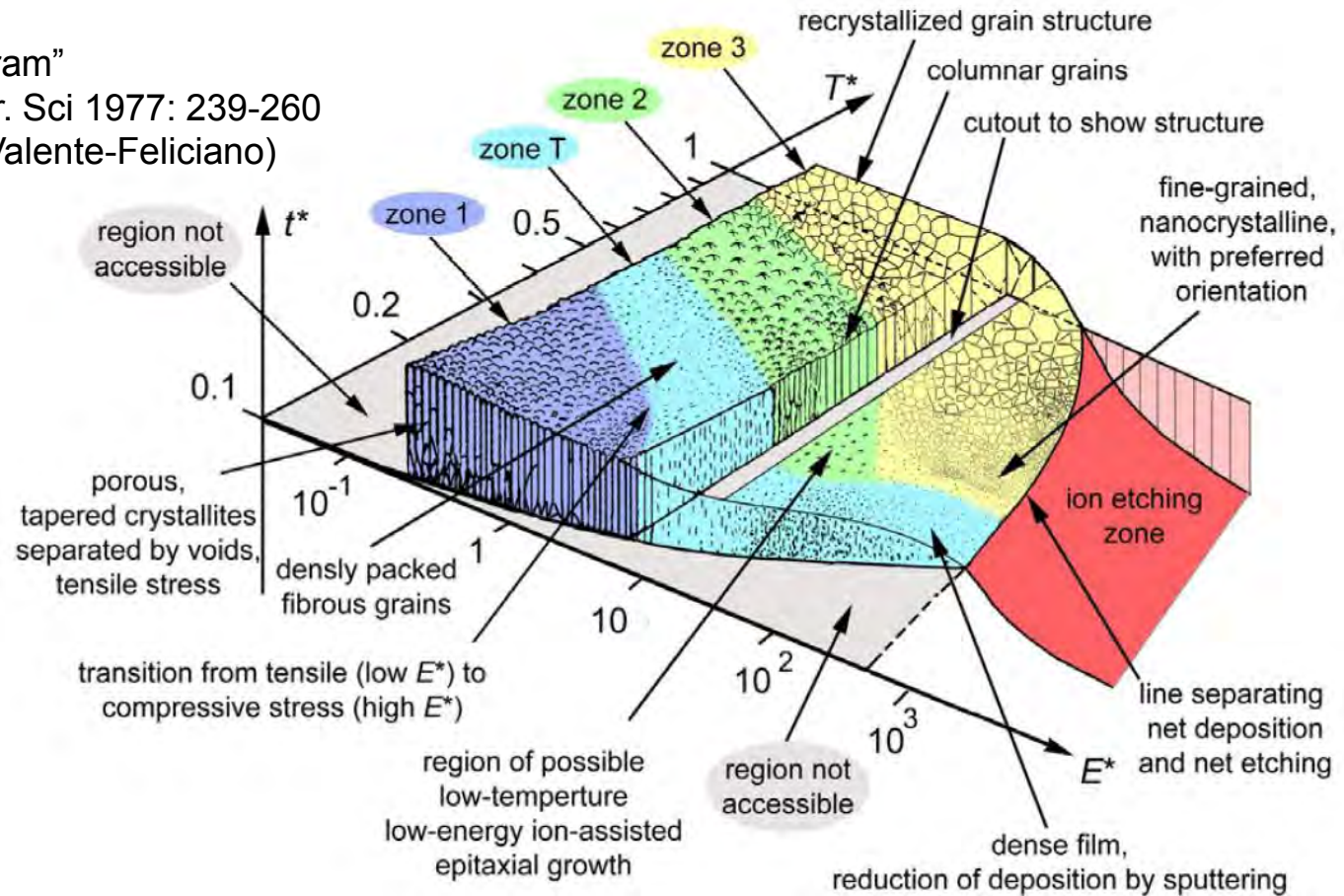
Structural absorber with transition wavelength $\lambda = 1 \mu\text{m}$

■ Structural absorber - morphology

“Thronton-Diagram”

Ann. Rev. Mater. Sci 1977: 239-260

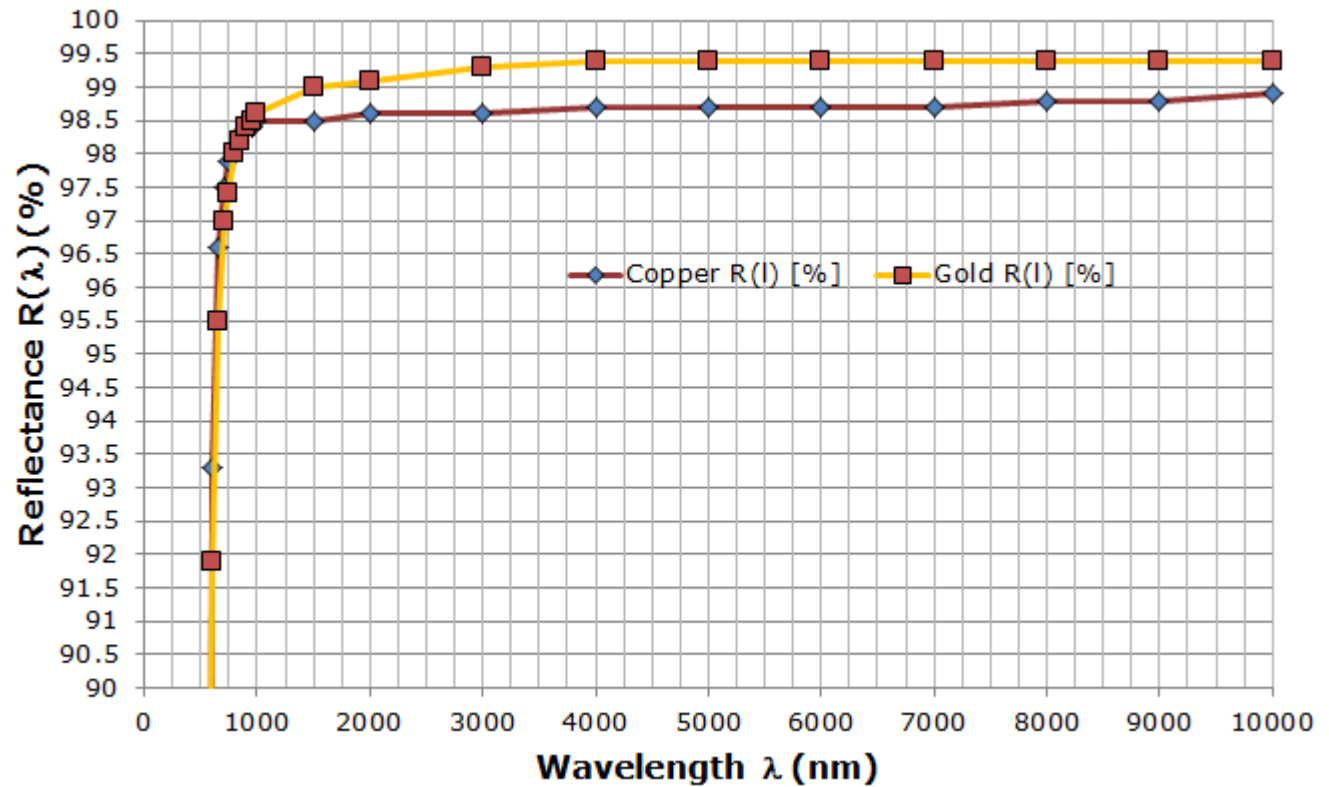
(Graph: A. -M. Valente-Feliciano)



“Physical (parameters) processes establishing structural zones” – film morphology.

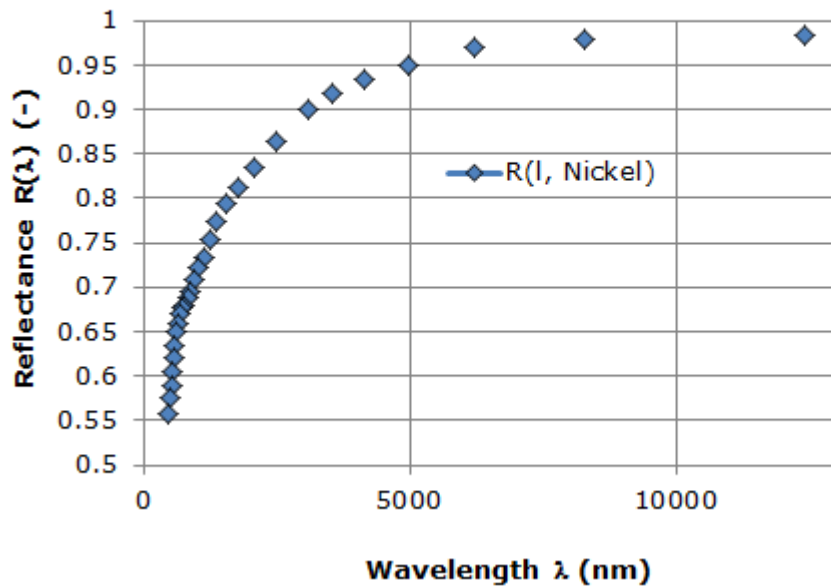
■ Substrates for “combined” absorbers

28 58.693 Ni NICKEL	29 63.546 Cu COPPER
46 106.42 Pd PALLADIUM	47 107.87 Ag SILVER
78 195.08 Pt PLATINUM	79 196.97 Au GOLD

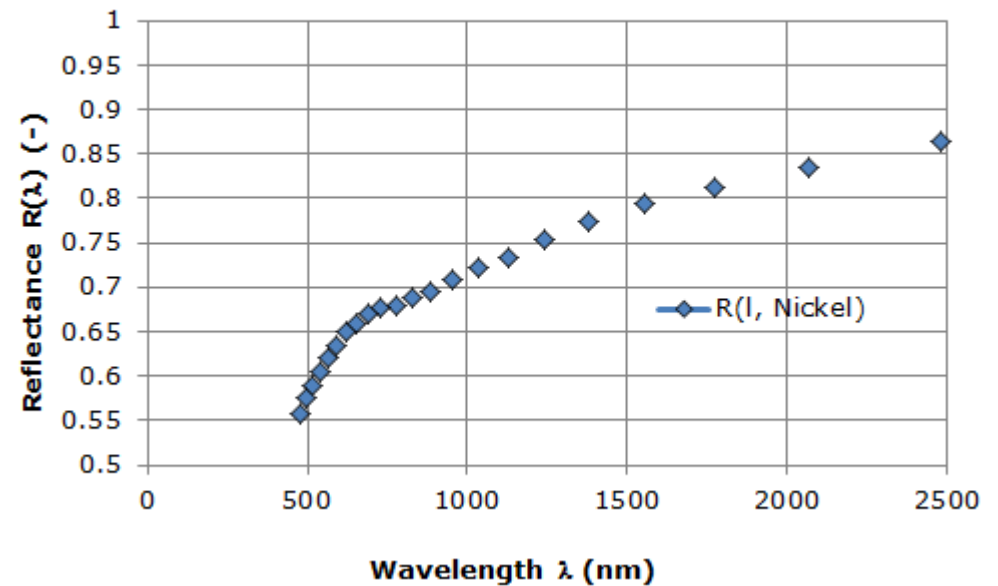


■ Substrates for “combined” absorber tubes

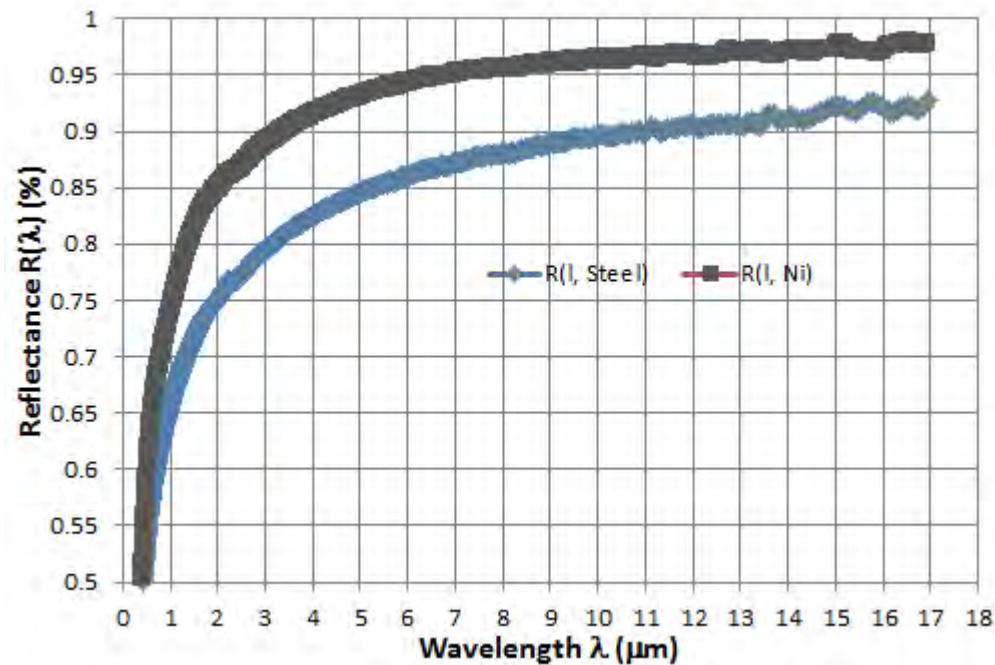
$R(\lambda, \text{Nickel})$



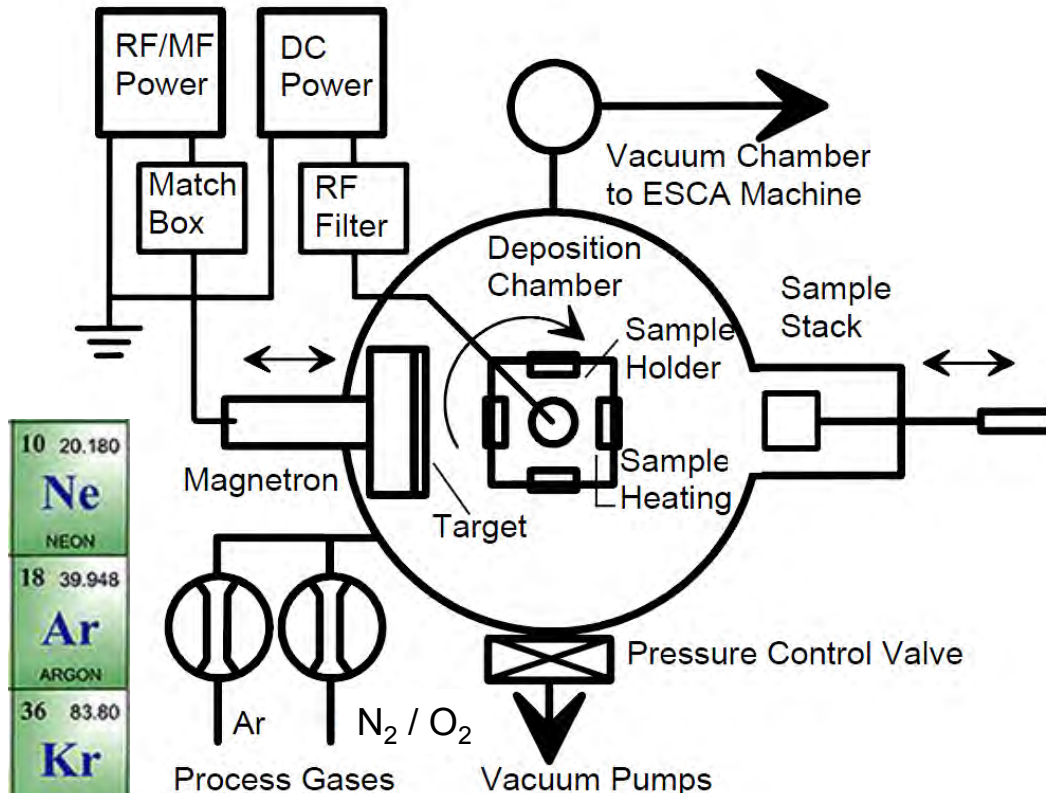
$R(\lambda, \text{Nickel})$



■ Substrates for “combined” absorber tubes



■ Plasma process for absorber preparation

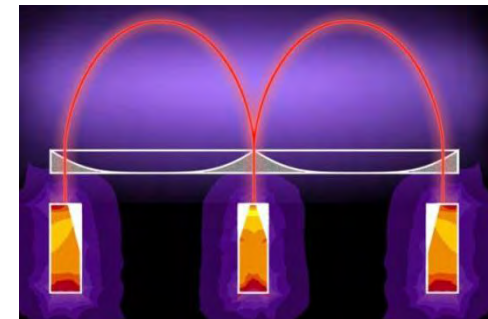
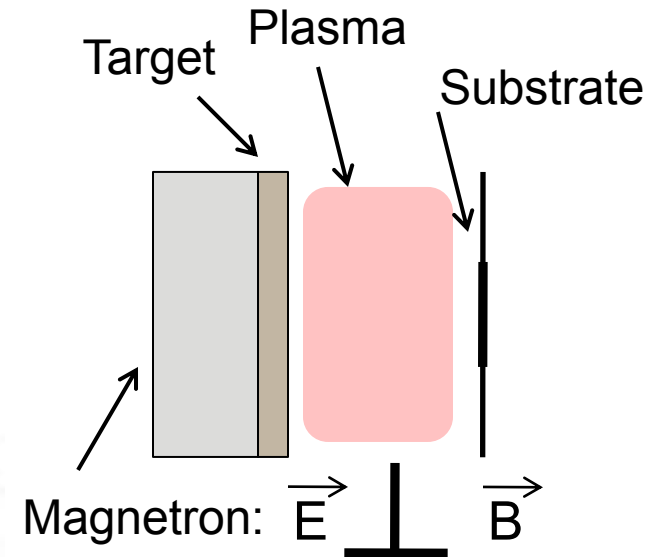


10	20.180
Ne	NEON
18	39.948
Ar	ARGON
36	83.80
Kr	KRYPTON
54	131.29
Xe	XENON

Reactive Magnetron Sputtering

Target Materials: Cr, W, Ti, ... Ag, Au, ... Nitrides ...)

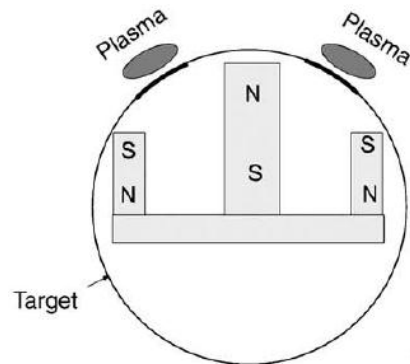
Process Gases: noble gases / reactive gases



www.angstromsciences.com

■ Plasma Process Technology Components

Magnetron Technology – planar / circular



D. Depla et al.
Plasma Deposition Processes



<http://www.vonardenne.biz>

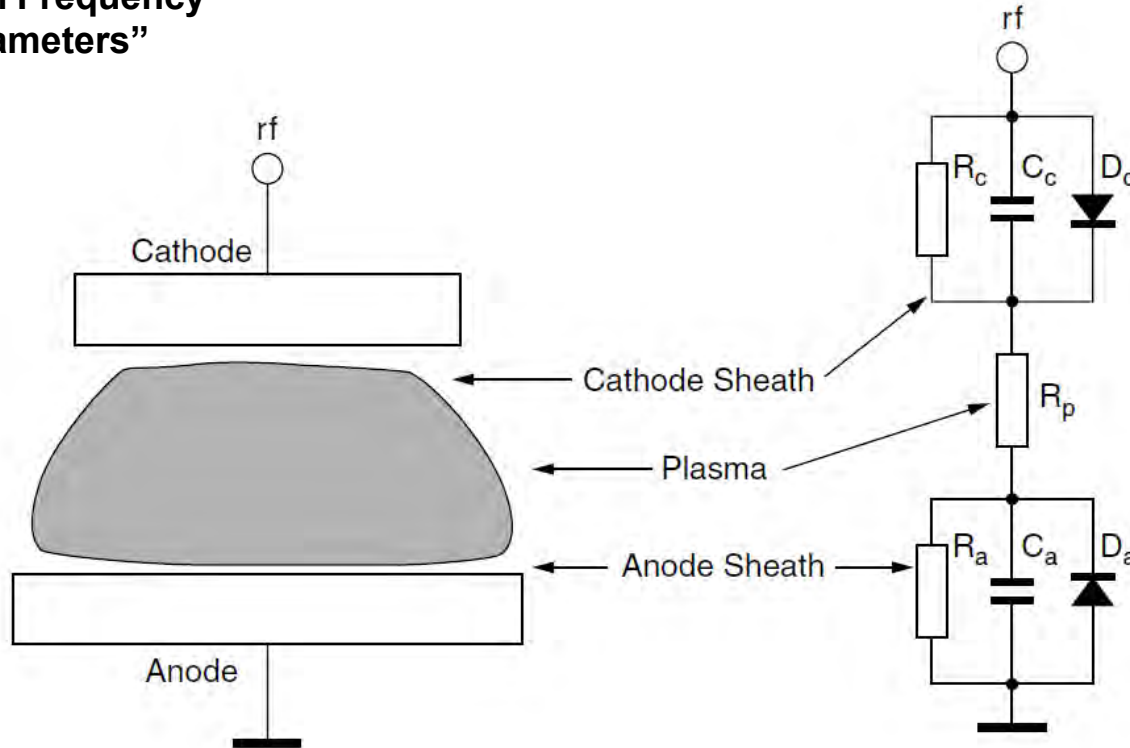


Magnetron Technology:

- <http://www.vonardenne.biz>
- <http://www.angstromsciences.com>

■ Coating Methods - RF excitation system

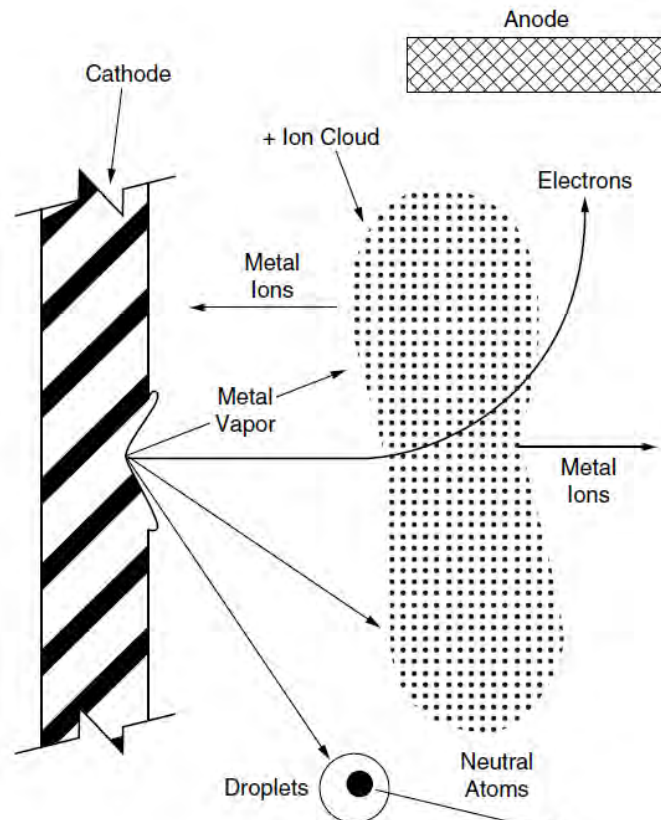
Plasma Ignition Frequency
Electrical “Parameters”



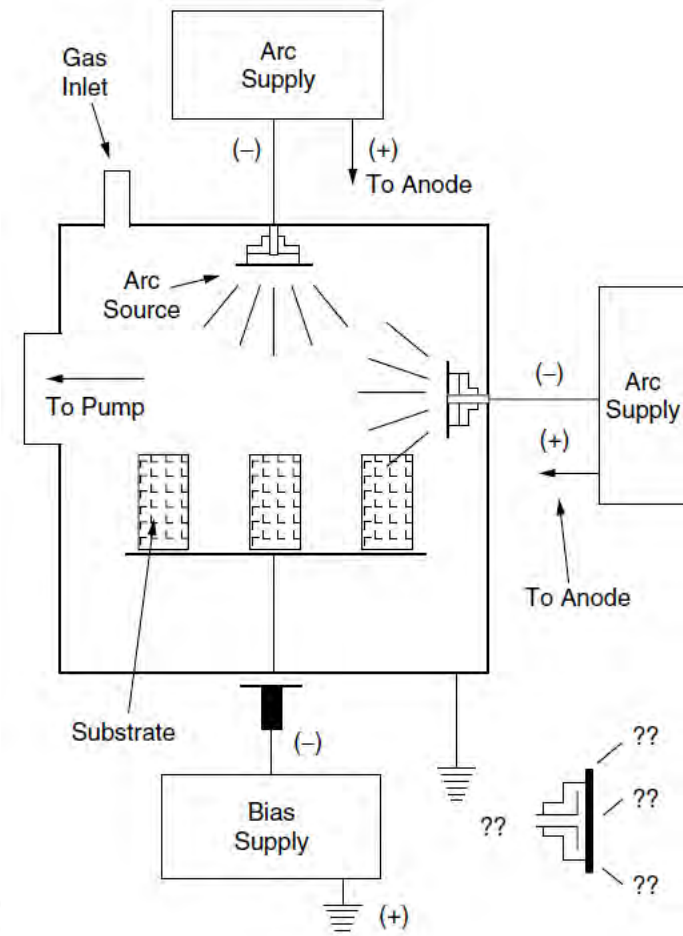
Lindas Pranevicius - Coating Technology Handbook

■ Coating Methods

Ion Energy / Sputter Yield
eV to K: $1\text{eV} \sim 1.16 \cdot 10^4 \text{K}$



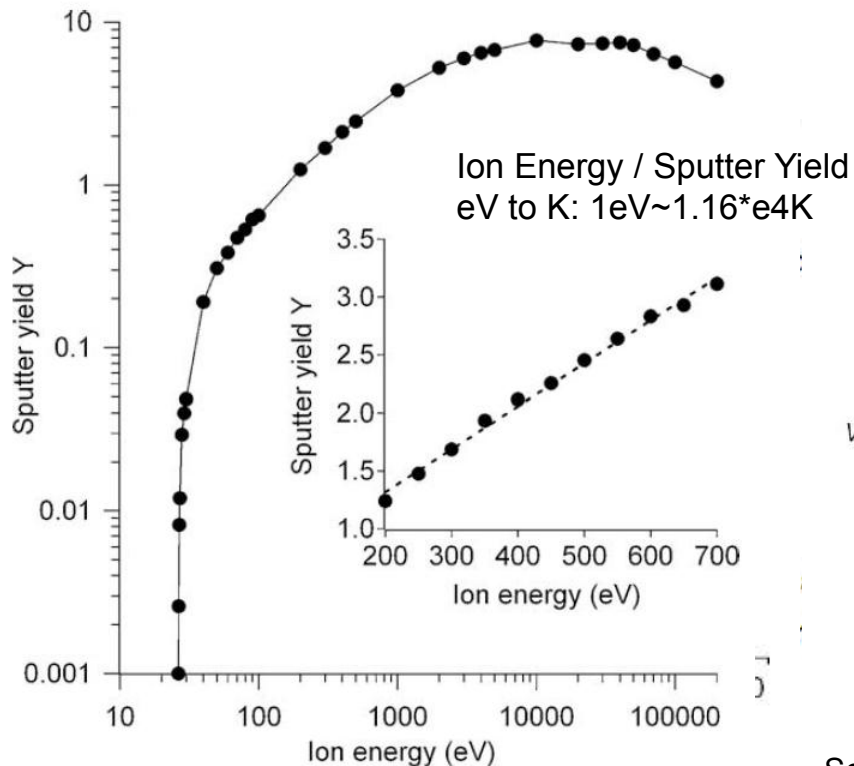
Emission characteristics of a cathodic arc source.



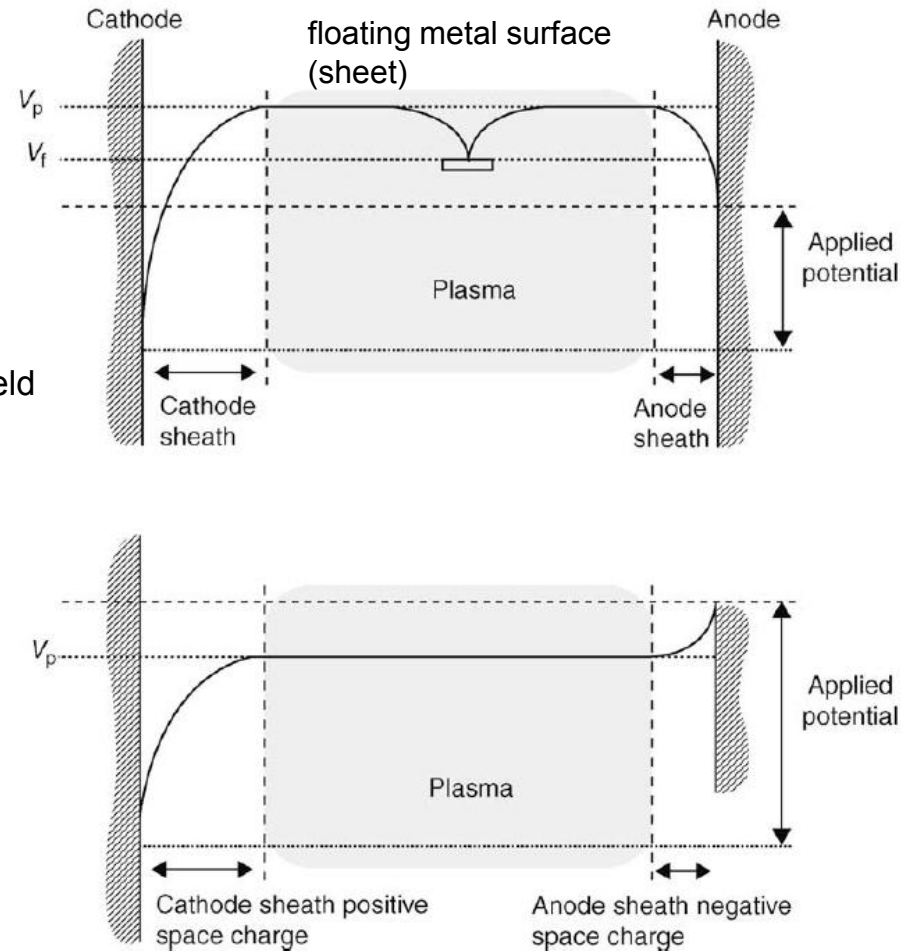
Schematic of a cathodic arc deposition system.

H. Randhawa - Coating Technology Handbook

■ Coating Methods / Plasma potential Electrical “Parameters” / Ion Energy



Sputter yield Y as a function of the Ar^+ ion energy at normal incidence in a magnetron sputtering process.



Schematic illustration of the plasma sheaths which form between a plasma apparatus walls for large anode and small anode.

Scott G. Walteon and J. E. Greene – Plasma Deposition Processes

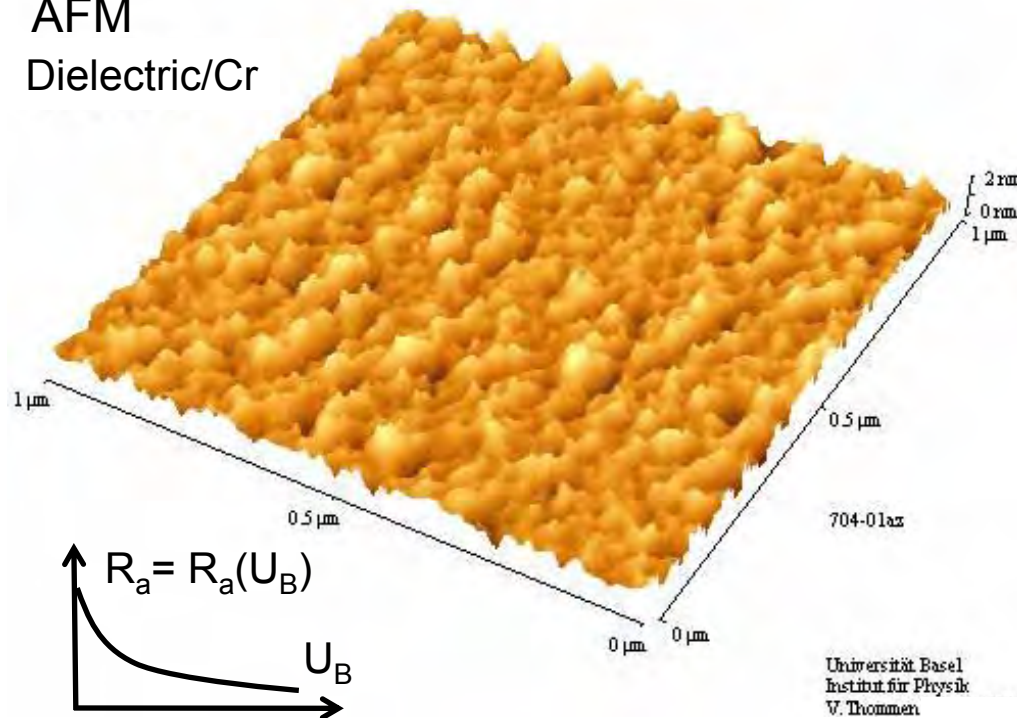
■ CERMET absorber surface

Substrate Bias Voltage

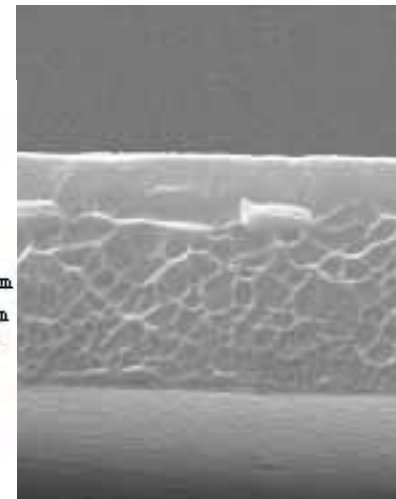
Surface roughness – optical & stability behaviour

AFM

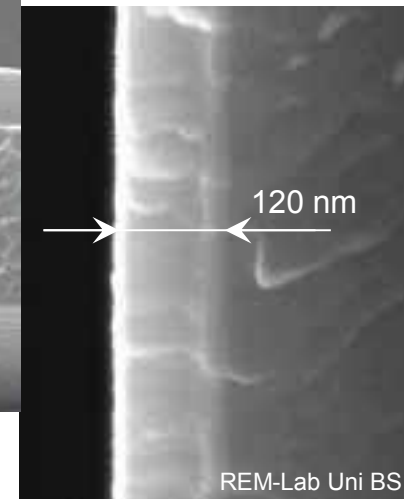
Dielectric/Cr



SEM

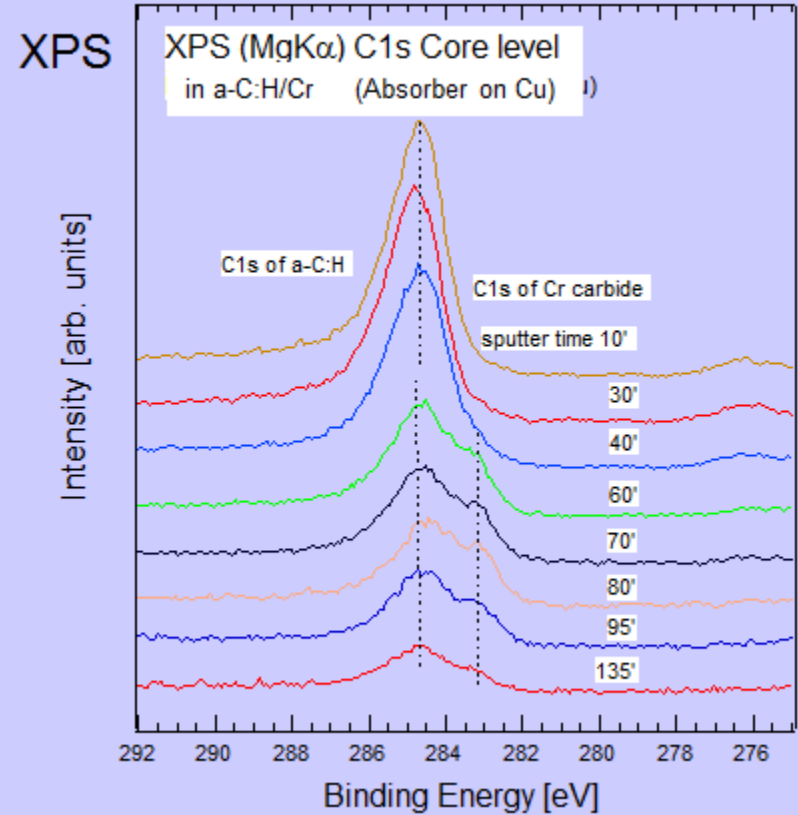
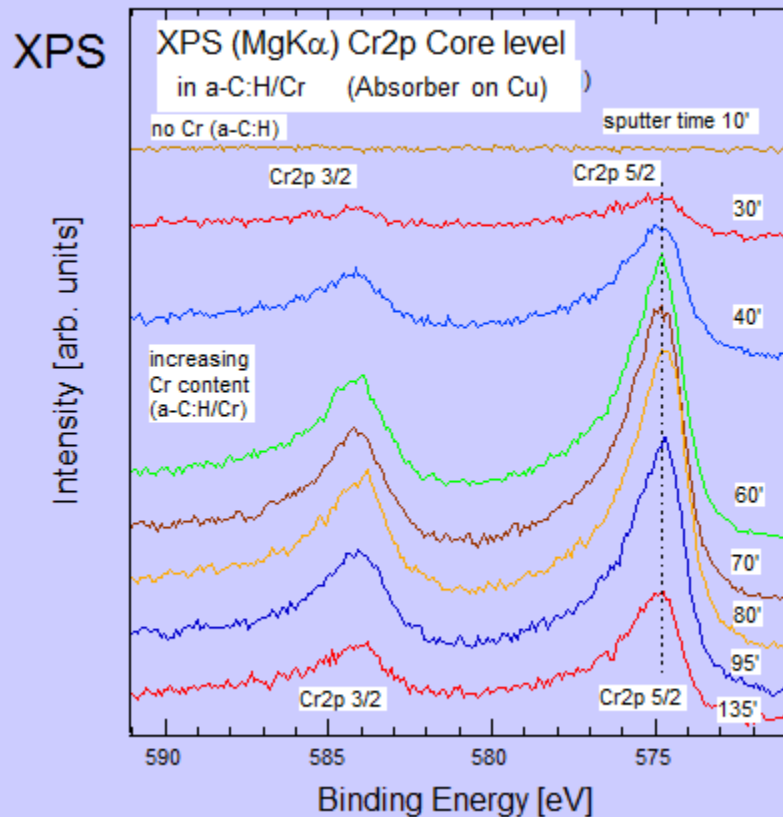


CERMET on Si



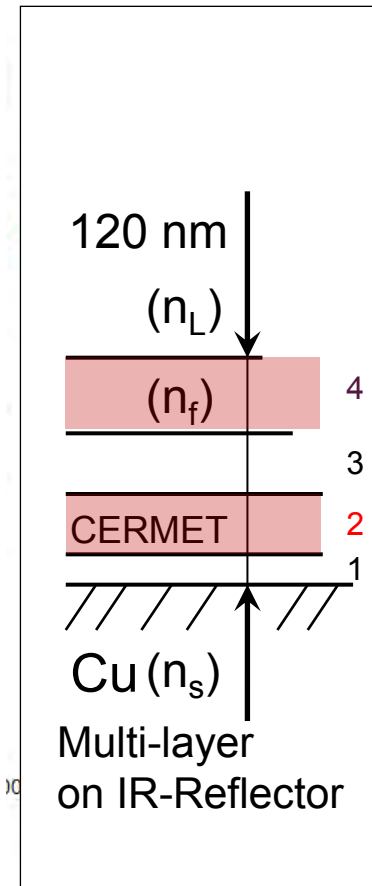
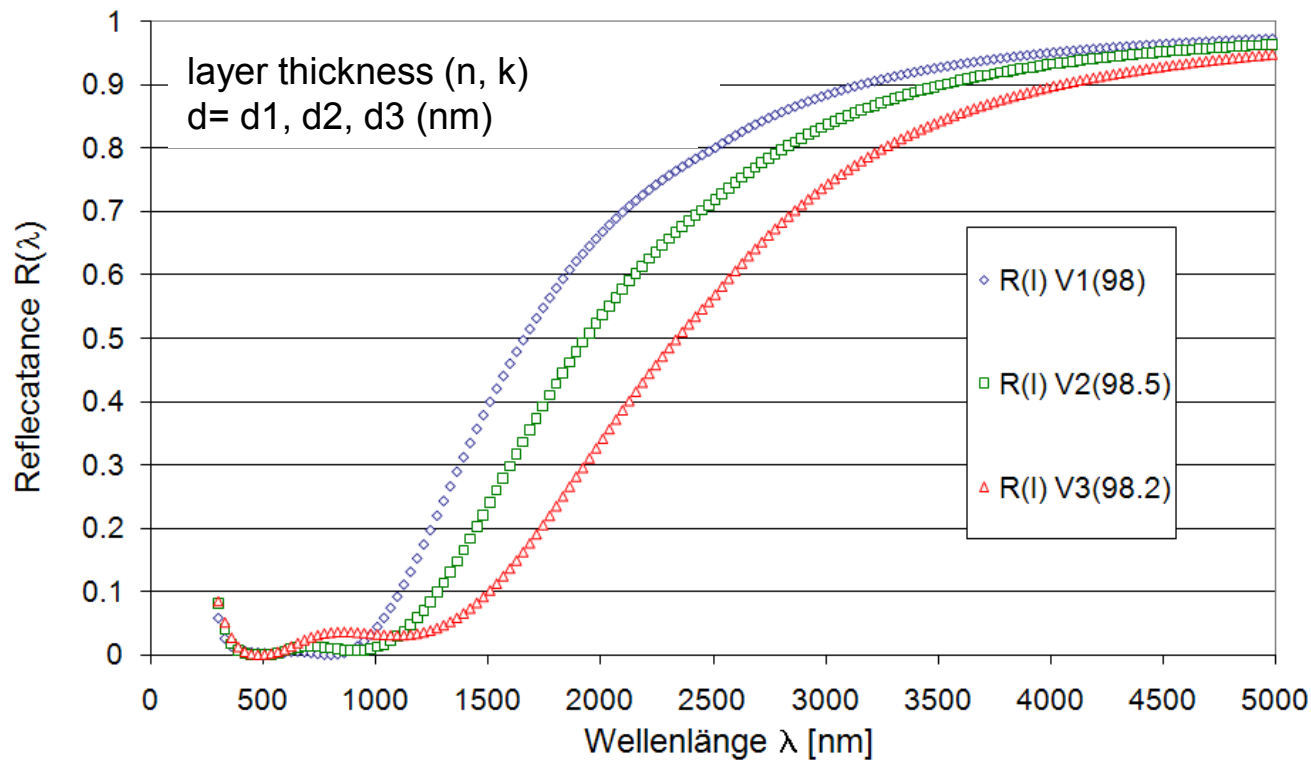
■ Chemical composition of an absorber coating

Process Gas Composition / Substrate Temperature rf-Power ...



Multilayer Absorber

Reflection $R(\lambda)$ in function of Wavelength λ - “sandwich layer”



■ Scale up of substrate bias - Plasma Potential variation

Absorber film properties depending of the plasma potential / Bias

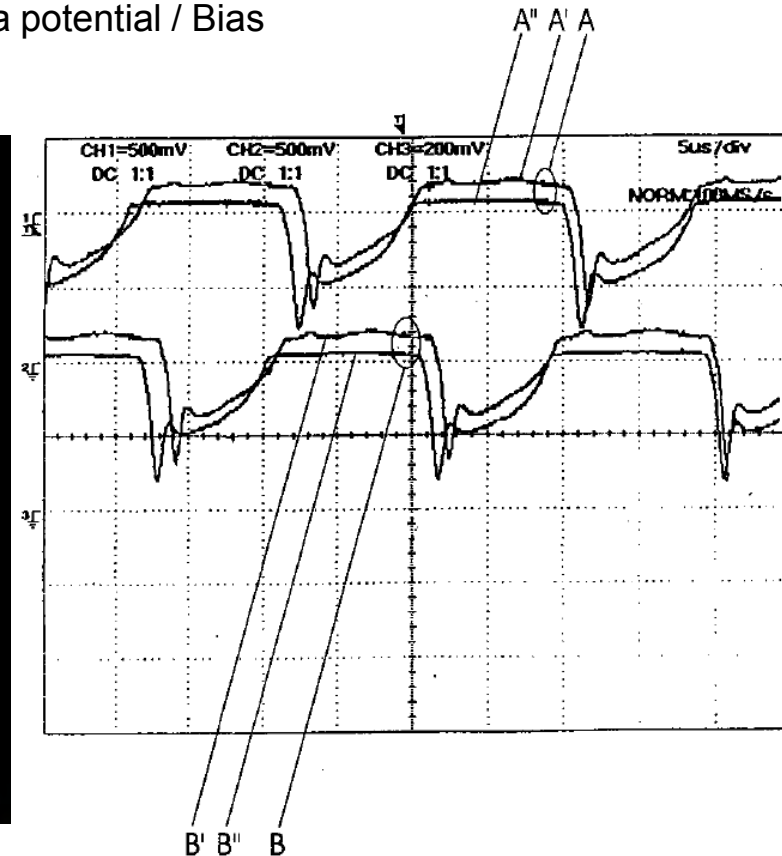
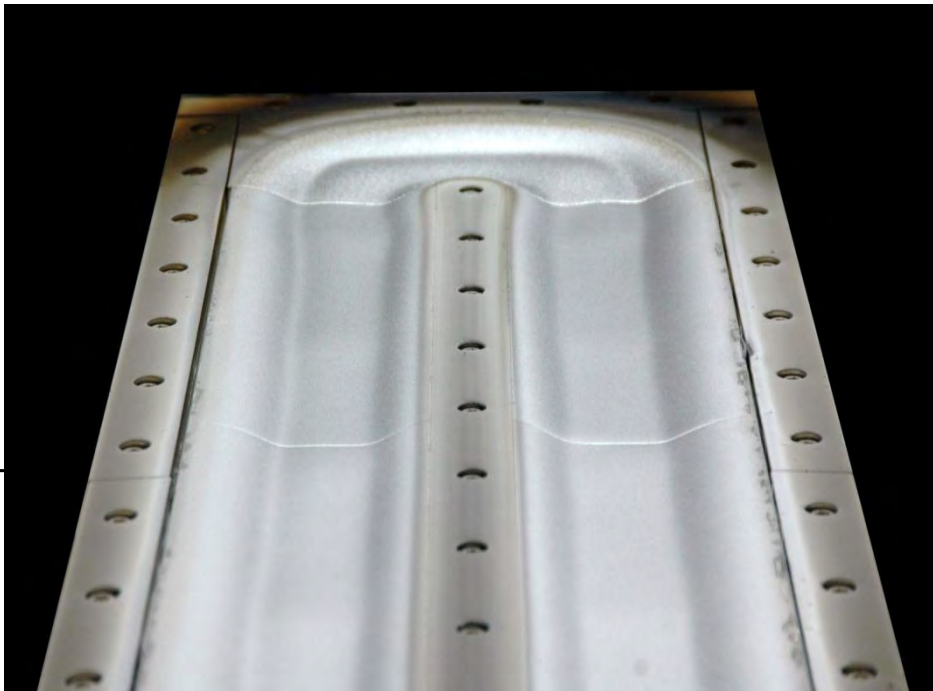
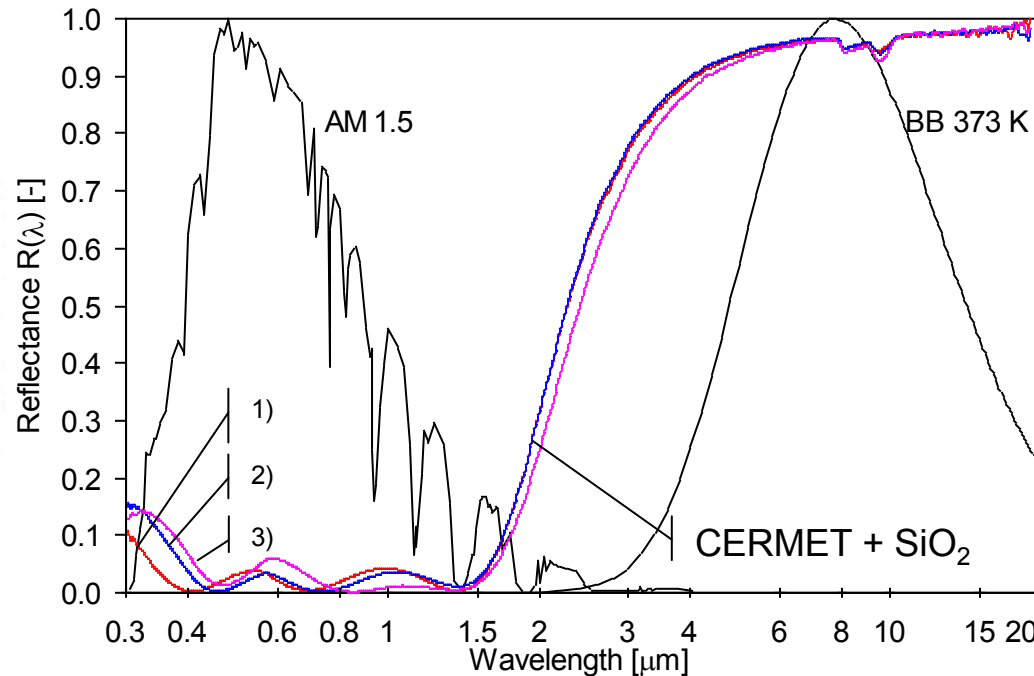


Fig. 2

Patentschrift: DE 198 30 404 B4

■ Multilayer solar selective absorber – Cermet / SiO₂



$R(\lambda)$ of three multilayer systems on copper metal sheets.
 $\alpha_{\text{sol}} = 95.0 \%$ to $\alpha_{\text{sol}} = 95.2 \%$; $\varepsilon_{\text{th}} = 3.1 \%$ to $\varepsilon_{\text{th}} = 3.7 \%$.

■ Absorber Coating Process

Parameter List (incomplete)

Geometry:	Substrate Surface Orientation to Plasma Source Vacuum Chamber design
Vacuum Chamber:	Base Pressure / Rest Gases Vacuum Pump Technology
Plasma Ignition:	Frequency (DC, MF, RF, HF) Plasma Generator Technology / Plasma Density
Reactant :	Coating Material Educt / Target Material / Process Gases Process Pressure / Plasma Density
Substrate:	Material (el. behaviour) Roughness Temperature Speed
Time:	Coating time

■ Tube Absorber Coating Machine Harding G. L.; US Patent 4309261 (1982)

FIG. 1

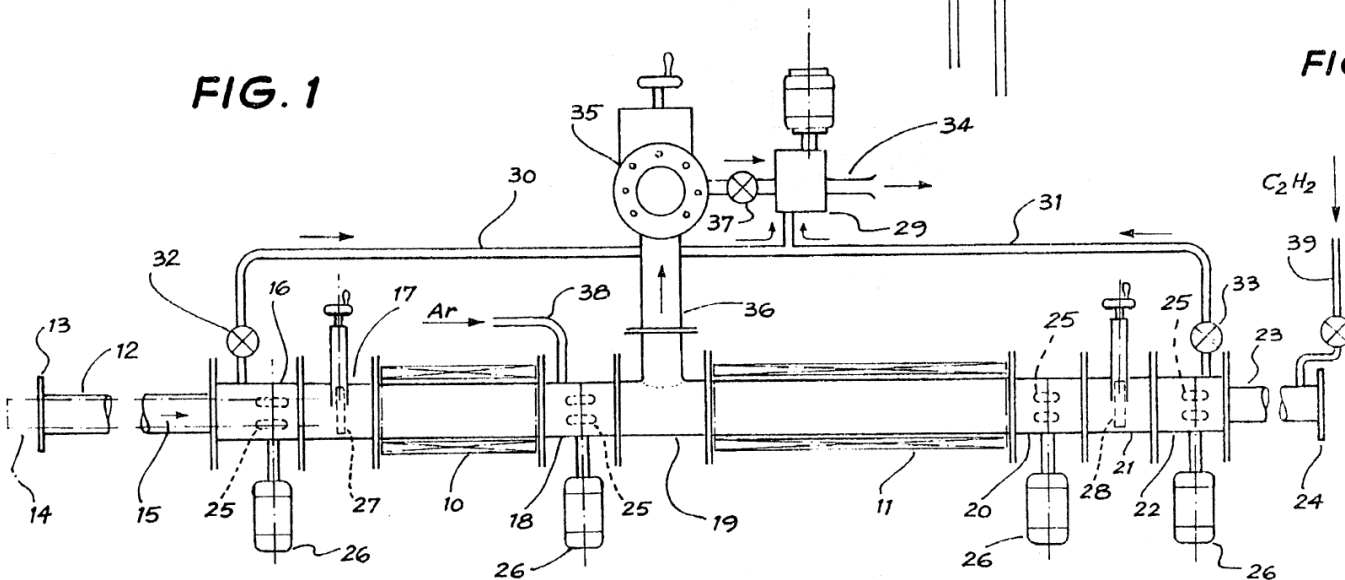
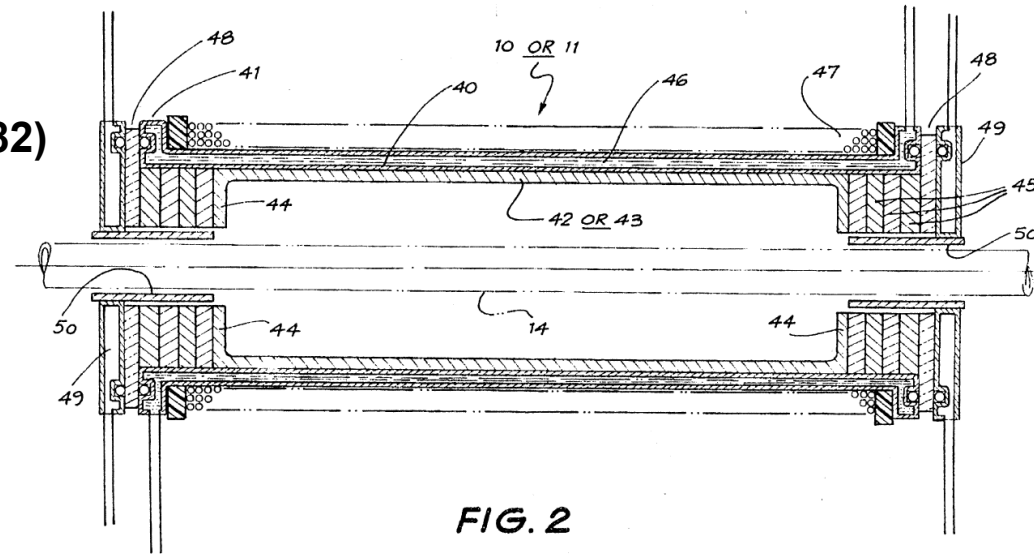
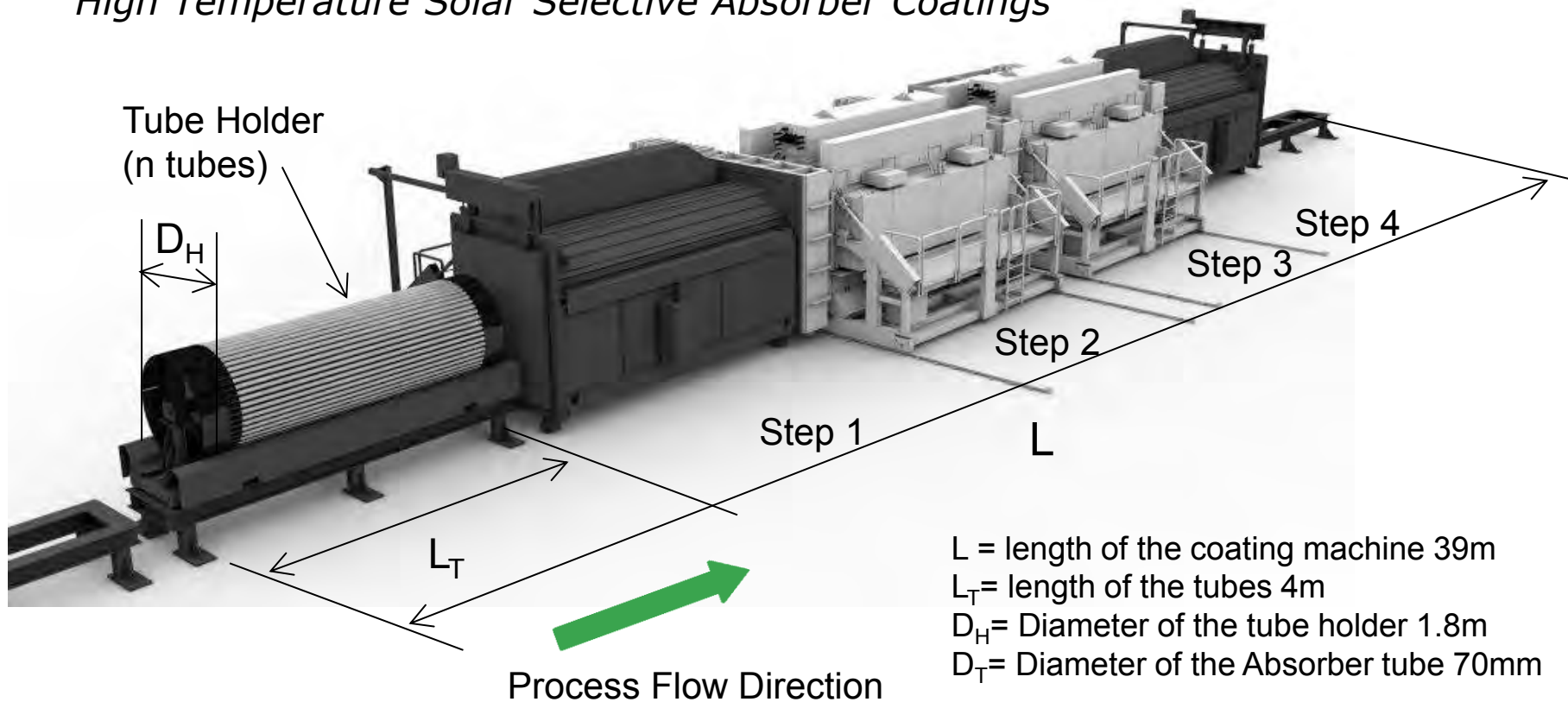


FIG. 2



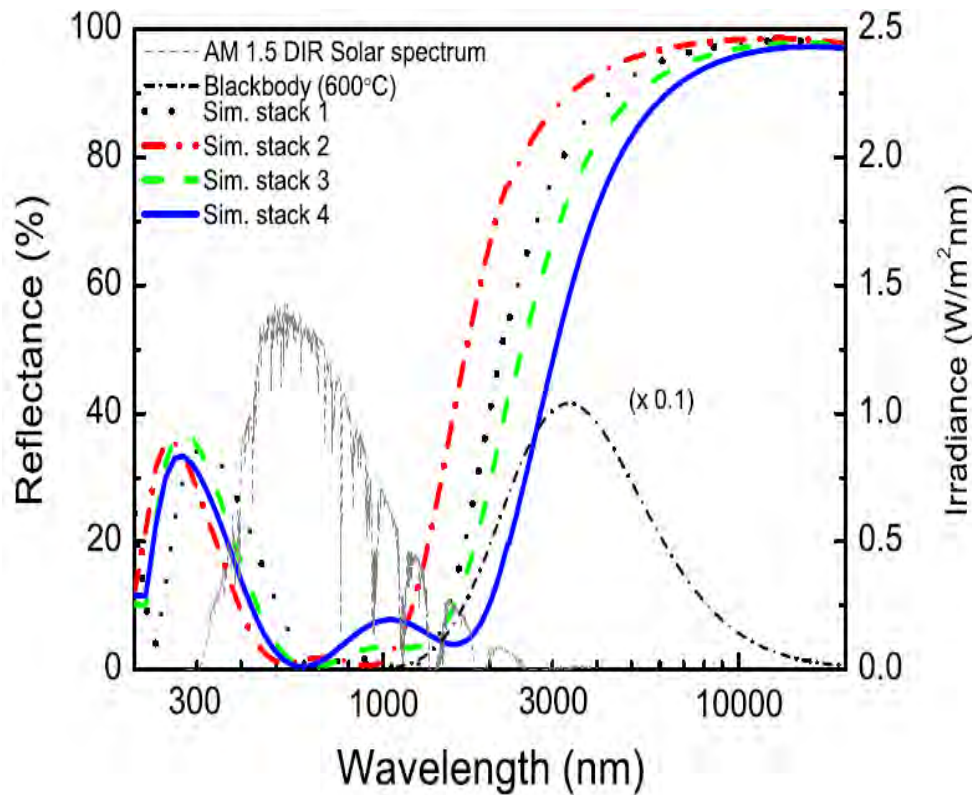
■ Tube Coating Machine

High Temperature Solar Selective Absorber Coatings



Source: Von Ardenne GmbH
Plattseite 19/29 | 01324 Dresden | Germany

Selective absorber - literature



CERMET Mo-Si₃N₄

R. Escobar-Galindo et al.



Thank you for your attention!



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